

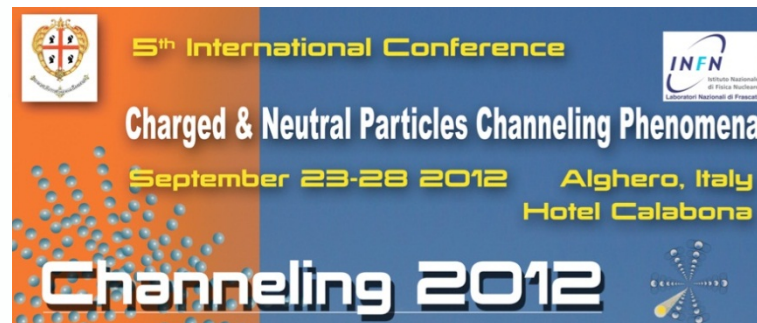
Channeling-2012

Doughnut Scattering of 255 MeV Electrons at $\langle 100 \rangle$ Axial Channeling in Thin Si Crystal

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T.A. Tukhfatullin¹

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²*Saga Light Source, Japan*



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- ❑ **Motivation:** «doughnut scattering» was observed first in high-energy channeling experiments using the proton and meson beams at CERN (U.Uggerhoj, The interaction of relativistic particles with strong crystalline field, NIMB, 252, 2006, 16-19)
- ❑ **Earlier theoretical consideration and Monte-Carlo calculations of similar effects for the case of electrons and positrons, was performed:** Shul'ga N F, Truten' S P 1982 Sov. Phys. Techn. Phys. 27 1399, Artru X, Fomin S P, Shul'ga N F 2005 Nucl. Instr. and Meth. in Phys. Res. B 230 476
- ❑ **Relativistic electron beam - early experiment (150 MeV):**



Nuclear Instruments and Methods in Physics Research B 252 (2006) 16–19

Beam Interactions
with Materials & Atoms

www.elsevier.com/locate/nimb

Electron beam deflection with channeling in a silicon crystal at the REFER electron ring

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H. Kuroiwa ^b, T. Ohnishi ^b, S. Sawada ^c

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- ❑ **A dependence of the deflection on the beam divergence, which indicated the possibility of using such a technique for beam diagnostics as well as beam handling was clearly observed**
- ❑ **Our work:** more detailed investigation & more correct computer simulations of relativistic electrons «doughnut scattering»



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SAGA Light Source (SAGA-LS)

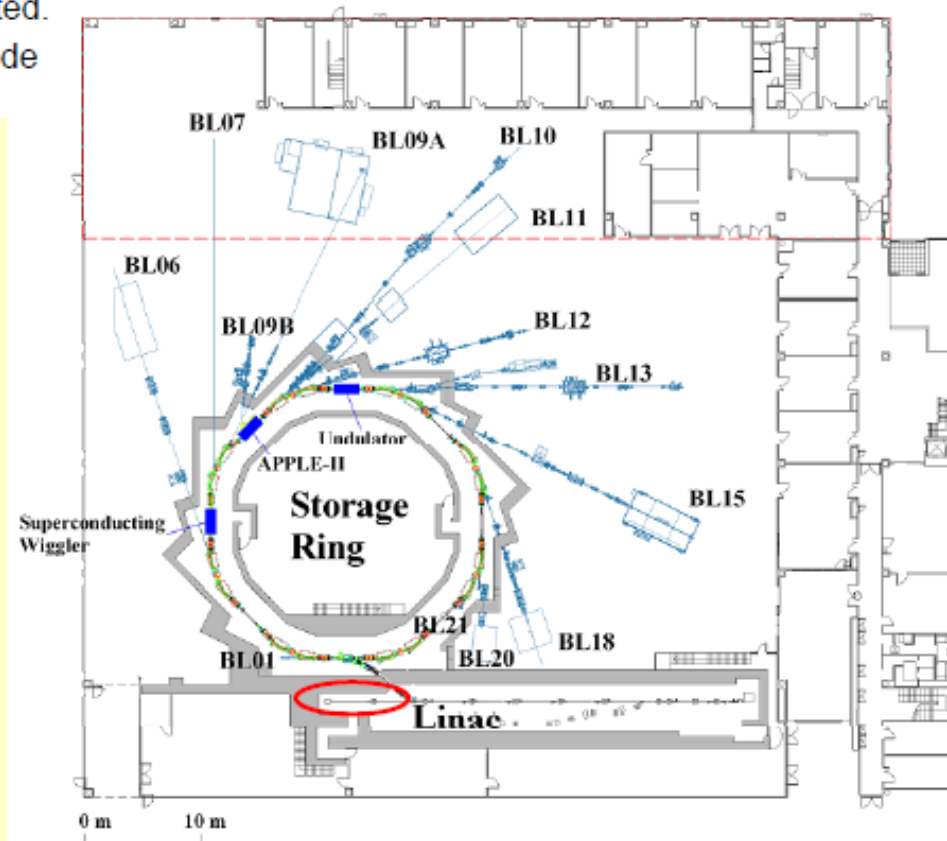
Operated by Saga Prefecture in Japan
In 2004, the accelerators were completed.
In 2006, the SAGA-LS started user-mode operation.

Storage Ring

Circumference	75.6 m
Energy	1.4 GeV
Stored Current	300 mA
Emittance	25 nm-rad
Lifetime	~7 hours @300 mA
Critical Energy	1.9 keV

Injector Linac

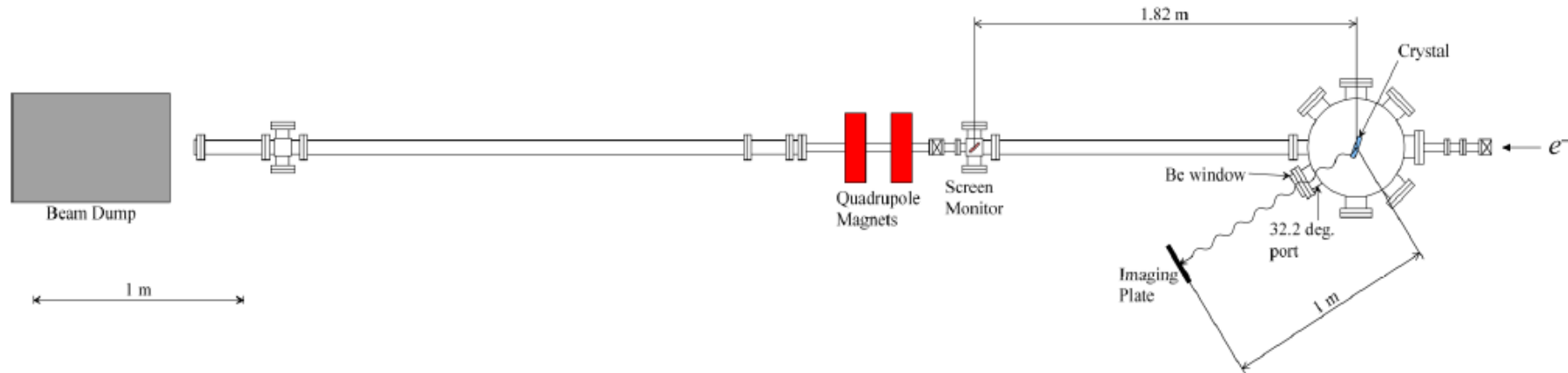
Total Length	30 m
Energy	255 MeV
Average Current	12 nA
Repetition	1 pps



SAGA Light Source, 8-7 Yayoigaoka, Tosu, Saga 841-0005, Japan

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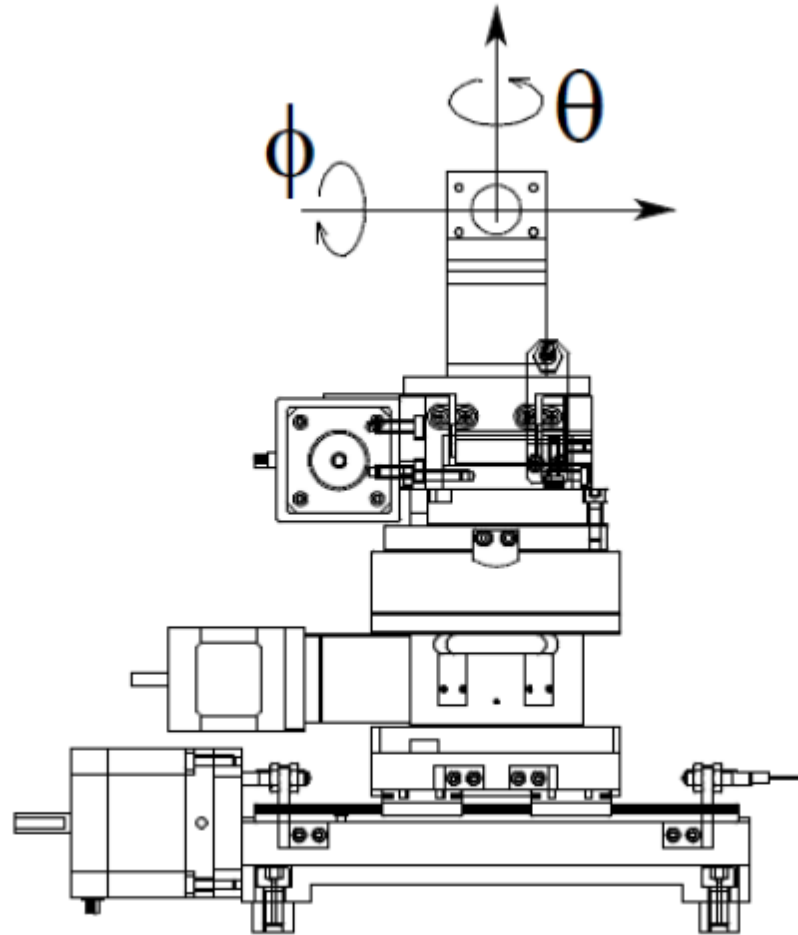
The Experimental Setup SAGA LS



- $\langle 100 \rangle$ channeling in Si crystal
- The beam energy: **$E = 255 \text{ MeV}$**
- Horizontal beam size: **0.2 mm**
- Vertical beam size: **0.7 mm**
- Horizontal angular divergence: **0.2 mrad**
- Vertical angular divergence: **0.3 mrad**
- Si crystal thickness: **$l=20 \text{ }\mu\text{m}$**

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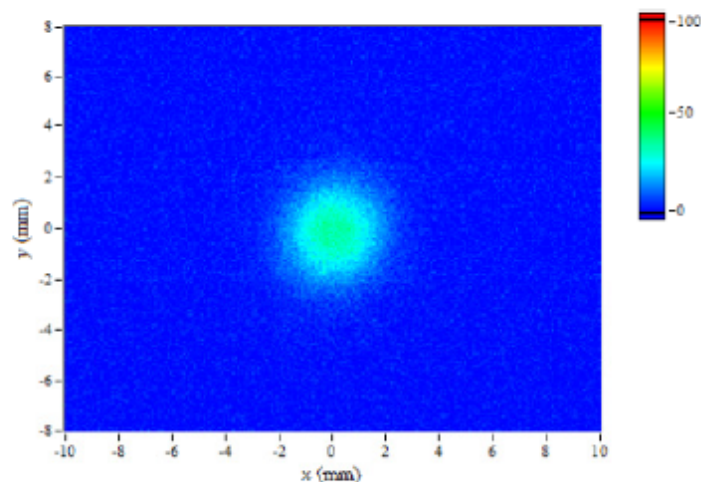
Goniometer



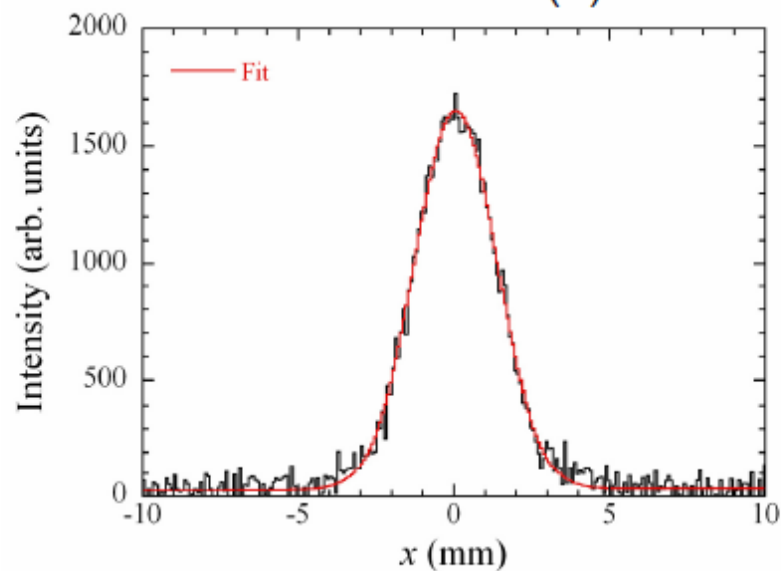
Angular step size **0.001°**

Data Analysis

$$(\theta, \phi) = (0^\circ, 0^\circ)$$

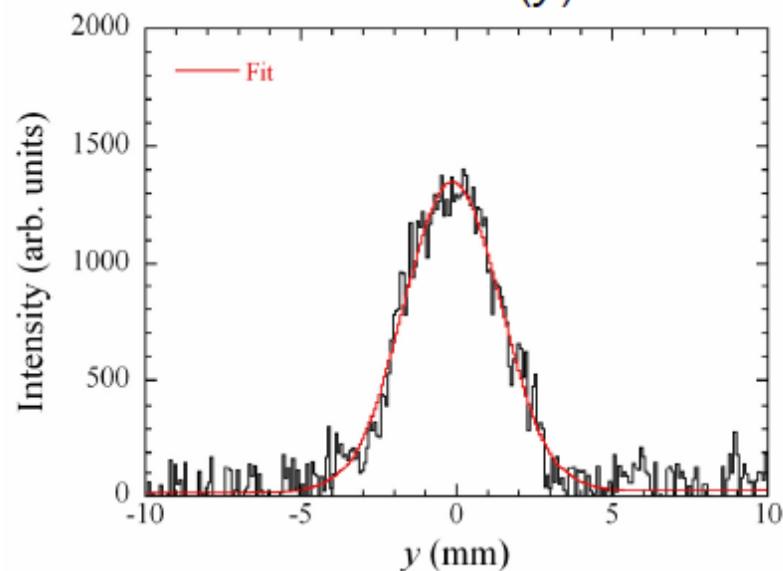


Horizontal (x)



$$I_x = I_{0,x} \exp\left[-\frac{(x - x_{peak})^2}{2\sigma_x^2}\right] + a_x x + b_x$$

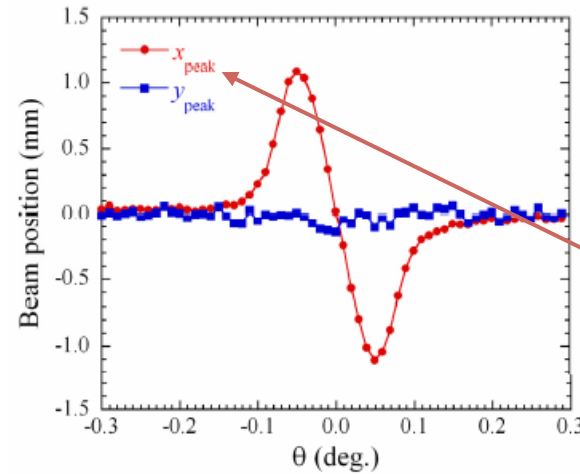
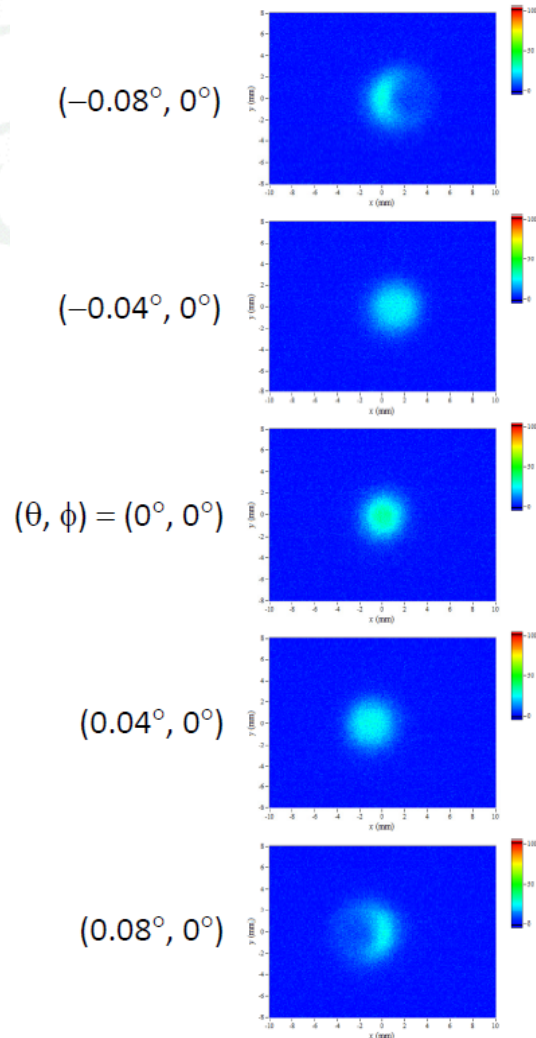
Vertical (y)



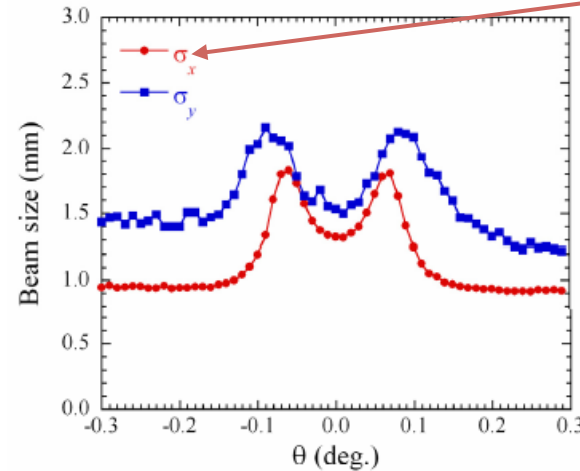
$$I_y = I_{0,y} \exp\left[-\frac{(y - y_{peak})^2}{2\sigma_y^2}\right] + a_y y + b_y$$

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The experimental results for <100> channeling in Si



$$I_x = I_{ox} \exp \left[-\frac{(x - x_{peak})^2}{2\sigma_x} \right] + a_x x + b_x$$



Electron trajectories simulation

- System of equations

$$\gamma m \ddot{x} = F_x = -\frac{\partial U(x, y)}{\partial x}$$

$$\gamma m \ddot{y} = F_y = -\frac{\partial U(x, y)}{\partial y}$$

- Initial conditions

$$x(0) \equiv x_0$$

$$y(0) \equiv y_0$$

$$v_x(0) = c \sqrt{1 - \frac{1}{\gamma^2}} \sin(\theta) \cos(\varphi)$$

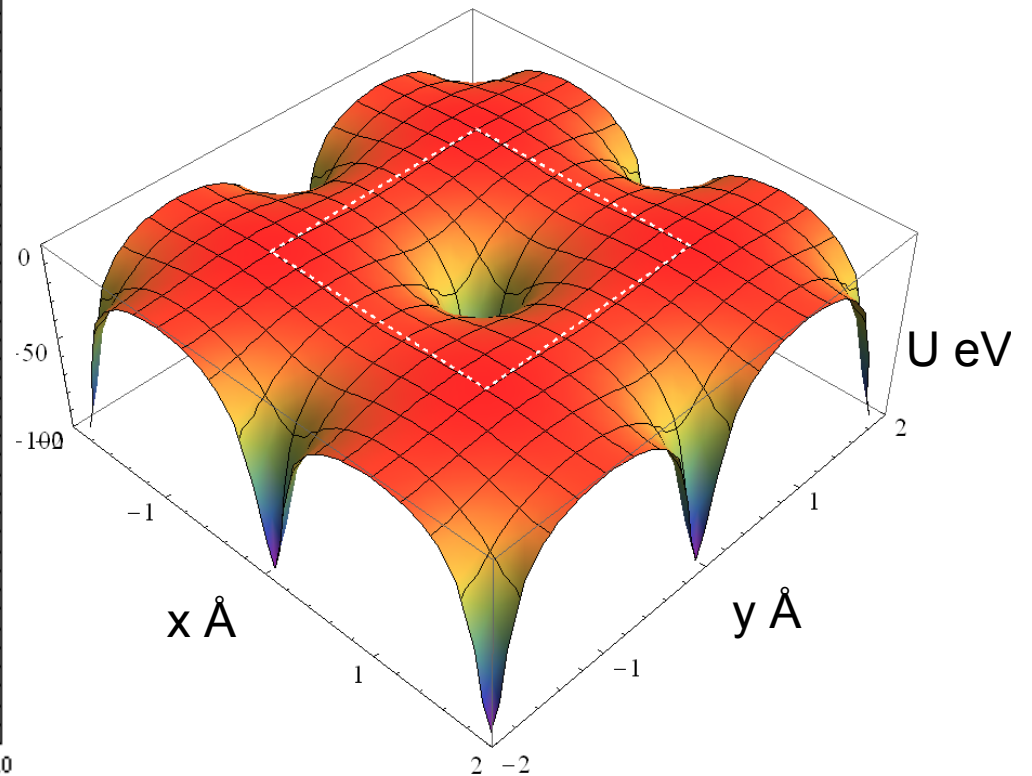
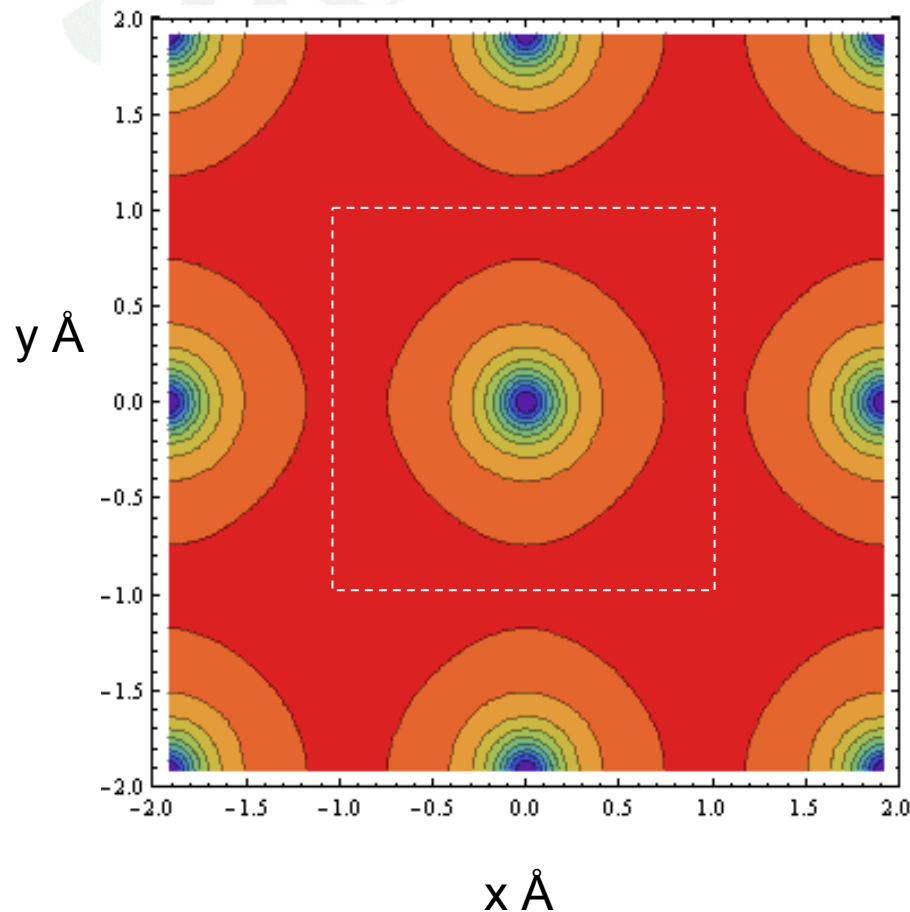
$$v_y(0) = c \sqrt{1 - \frac{1}{\gamma^2}} \sin(\theta) \sin(\varphi)$$

**Bogdanov O. V., Fiks E. I.,
Korotchenko K. B., Pivovarov Yu. L.
and Tukhfatullin T. A. Basic
channeling with Mathematica©: A
new computer code// J. Phys.: Conf.
Ser. V. 236, 1, 2010, 012029**

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Simulation results two-dimensional potential of the crystallographic axes

$$U(x, y) = eV(x, y) = e \sum_k V_{ax}(x - kd_{xp}, y - kd_{yp})$$

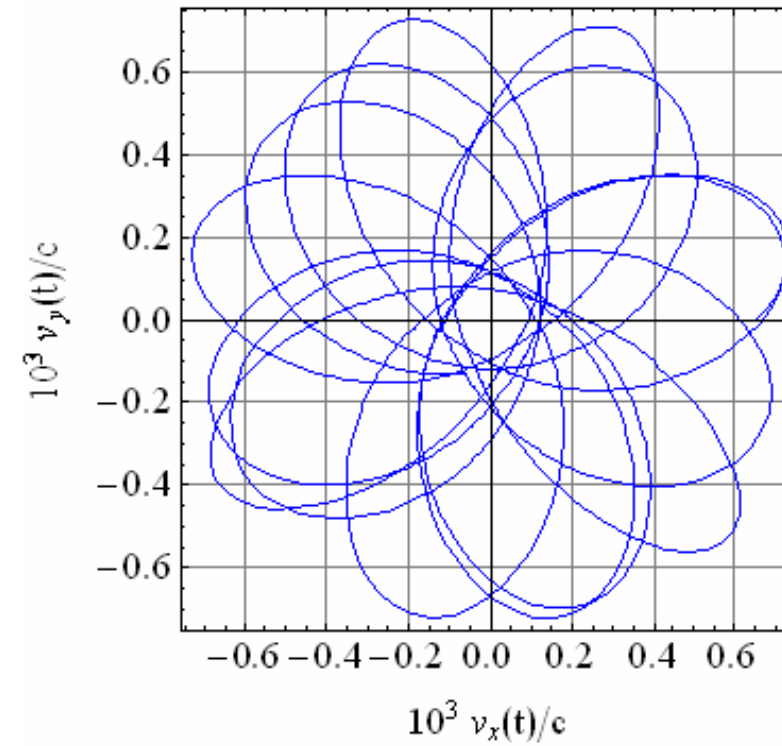
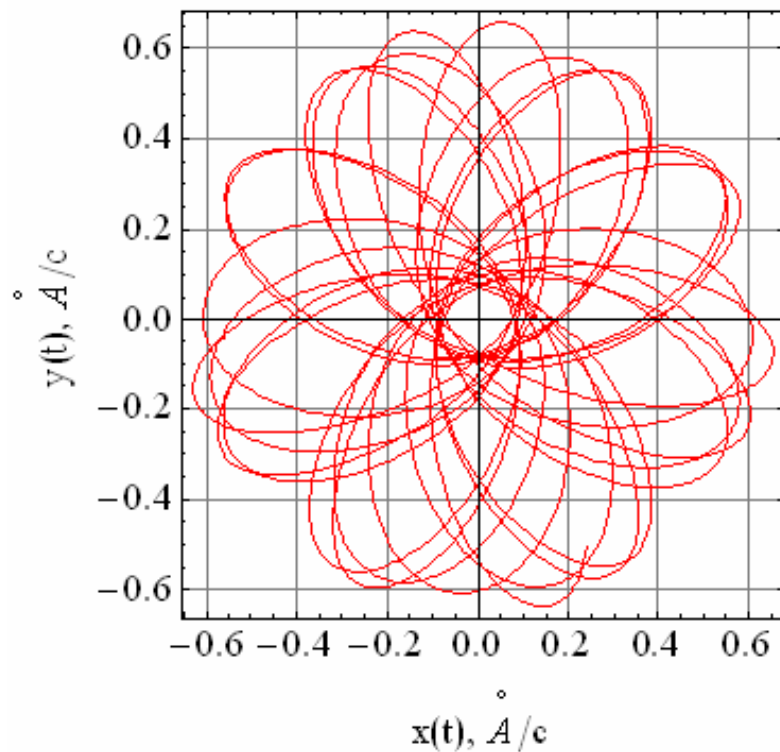


Doyle P.A. and Turner P. S.// Acta Cryst.
1967 A24, 390

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Simulation results trajectories

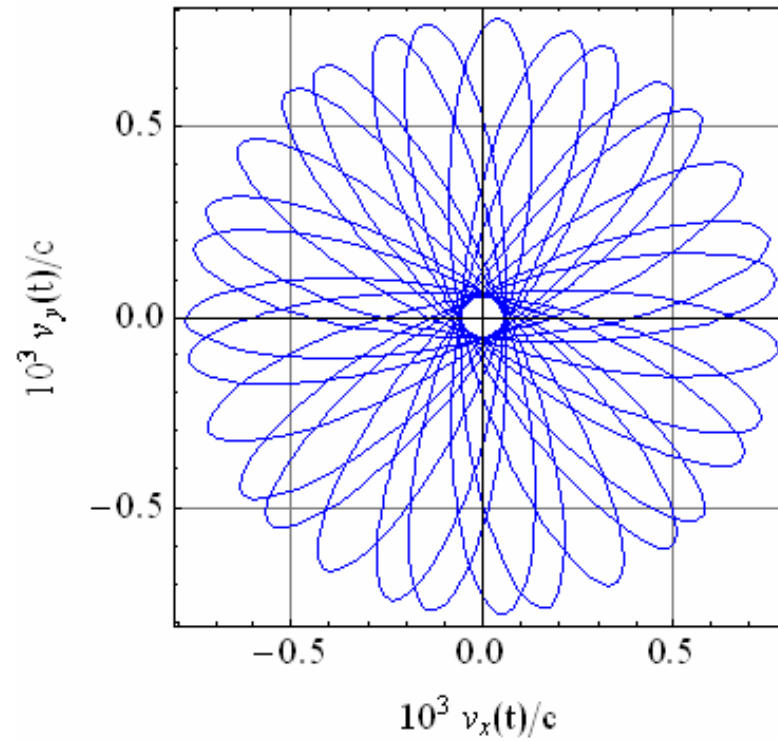
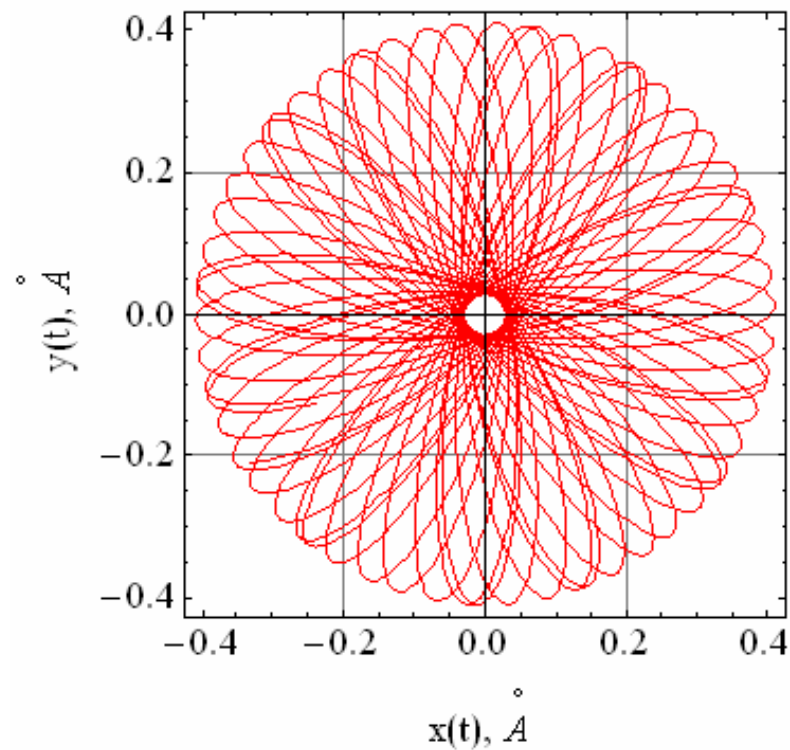
$\theta=0.037^\circ$, $\varphi=0.01^\circ$, $E = 255$ MeV, $\langle 100 \rangle$ Si, $l=20$ μm



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Simulation results trajectories

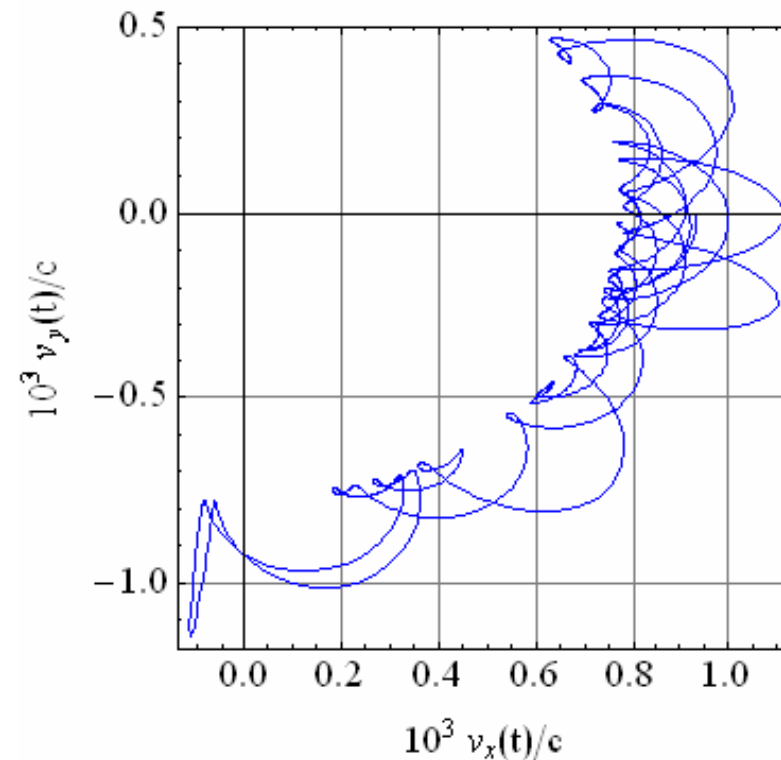
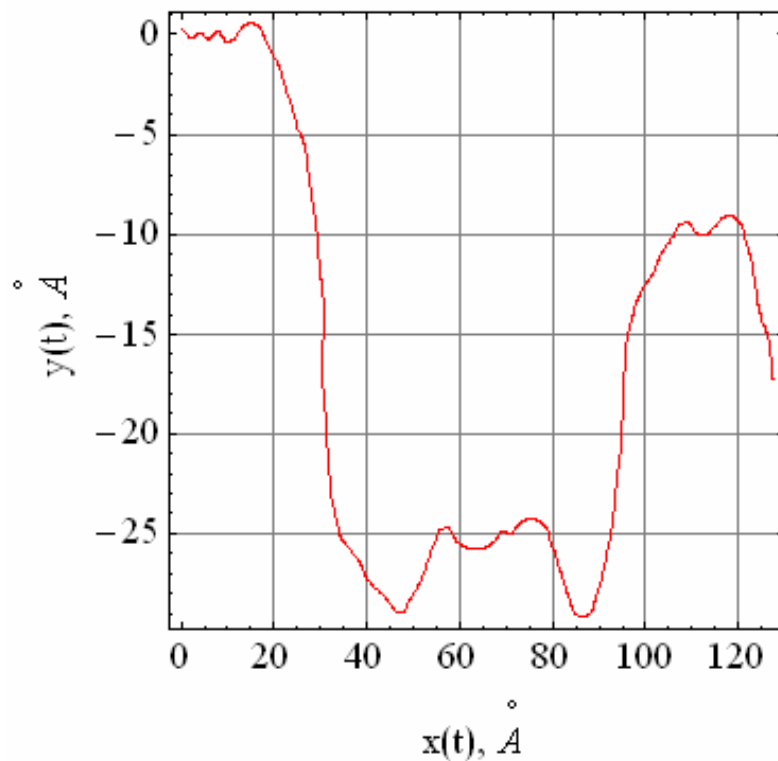
$\theta=0.062^\circ$, $\varphi=-0.028^\circ$, $E = 255$ MeV, $\langle 100 \rangle$ Si, $l=20$ μm



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Simulation results trajectories

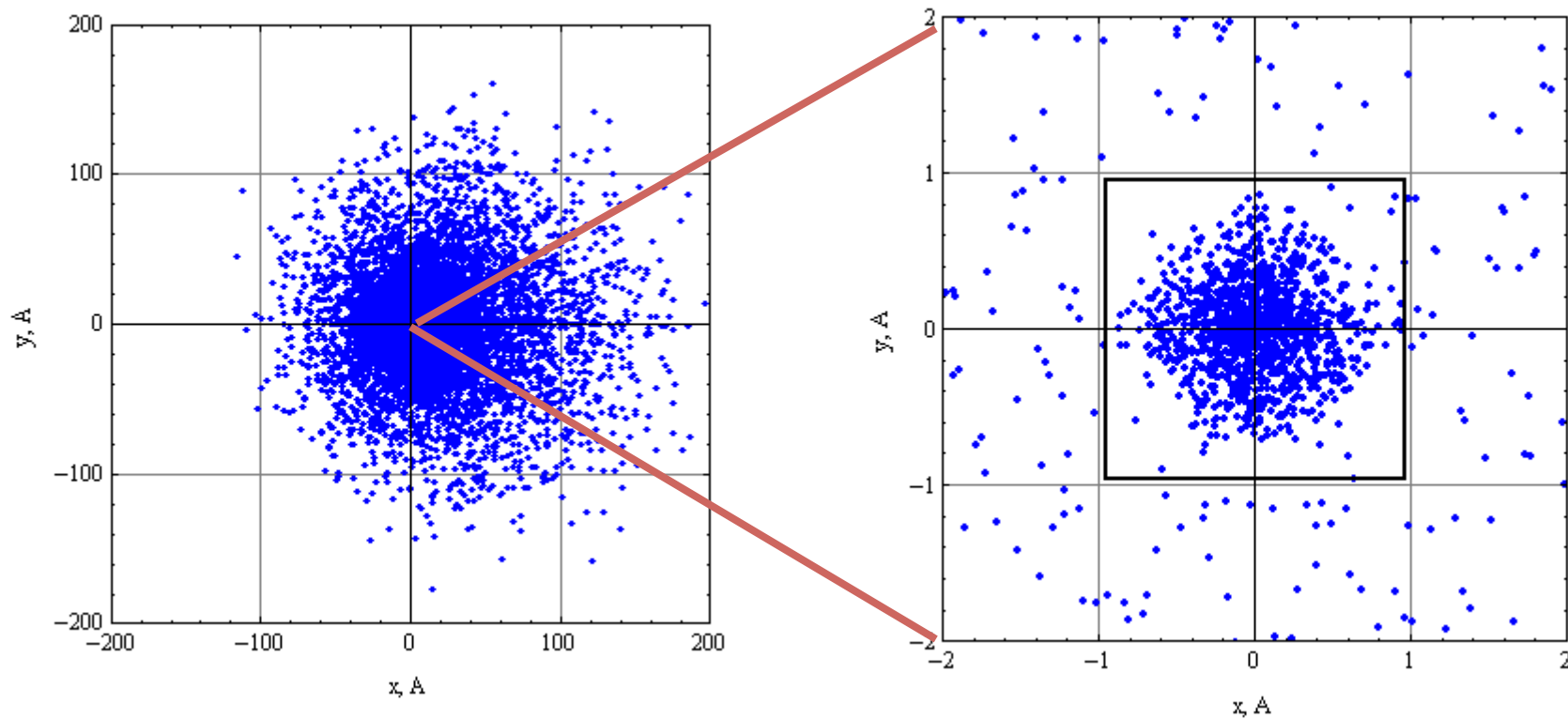
$\theta=0.053^\circ$, $\varphi=-0.036^\circ$, $E = 255$ MeV, $\langle 100 \rangle$ Si, $l=20$ μm



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Simulation results exit points of the particles

$\theta=0.025^\circ$, $\varphi=0.0^\circ$, $E = 255 \text{ MeV}$, $\langle 100 \rangle \text{ Si}$, $l=20 \mu\text{m}$



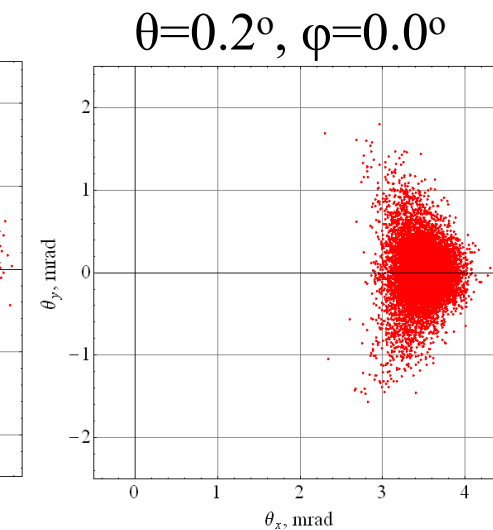
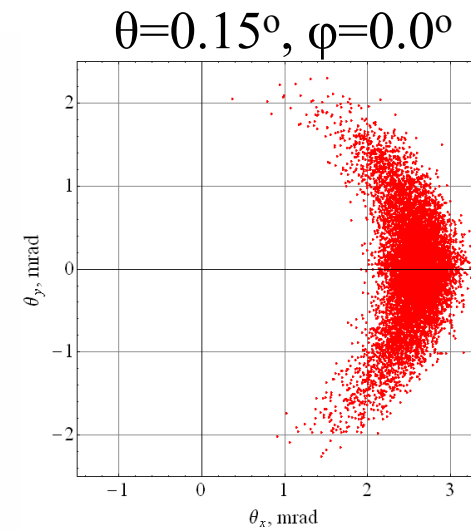
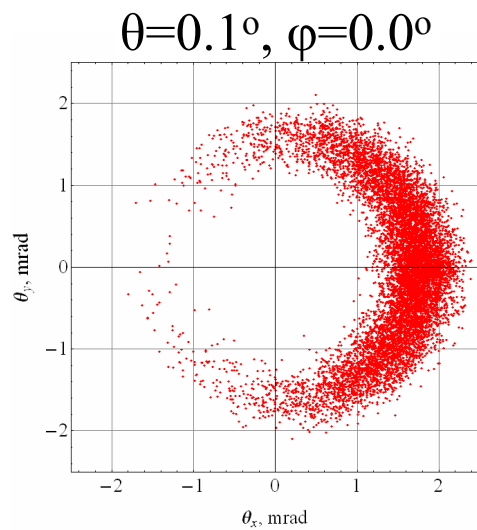
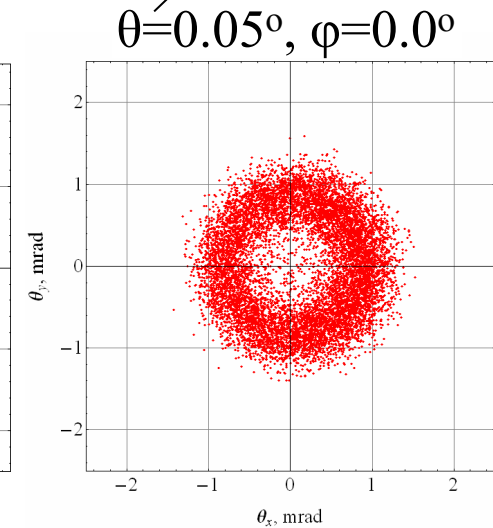
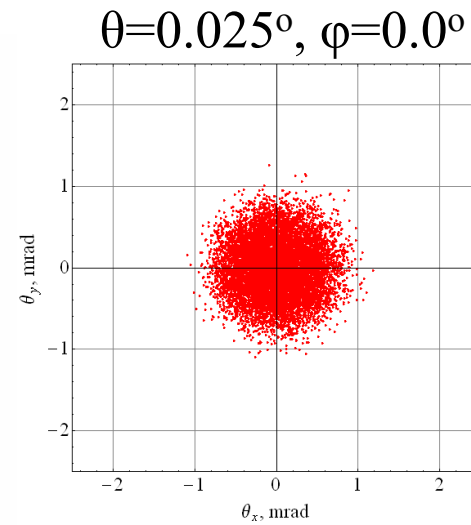
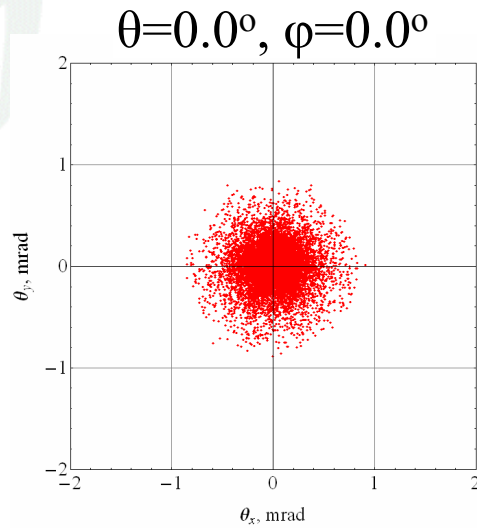
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Simulation results

electrons angular distributions

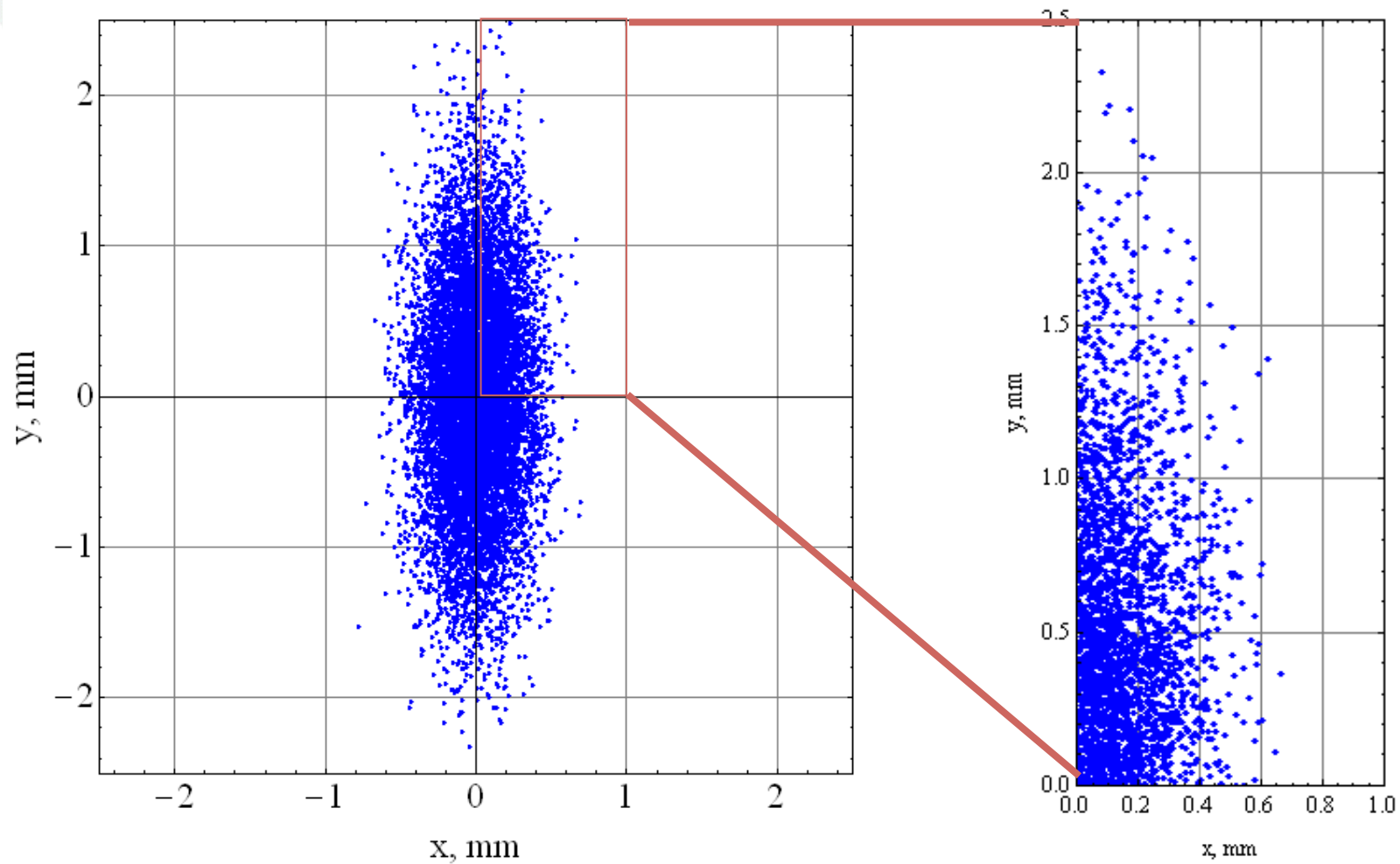
Critical angle

$$\theta_x = v_x(l)/c$$
$$\theta_y = v_y(l)/c$$



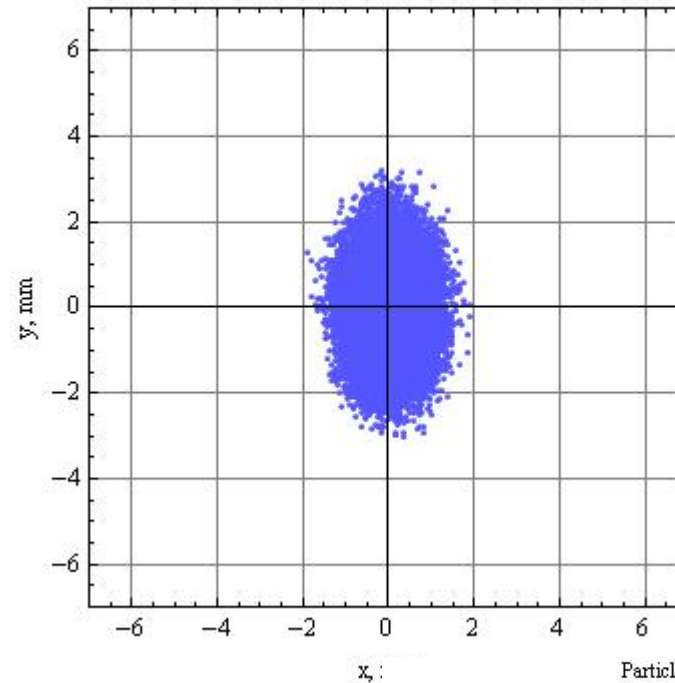
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Simulation results SAGA-LS incident beam profile

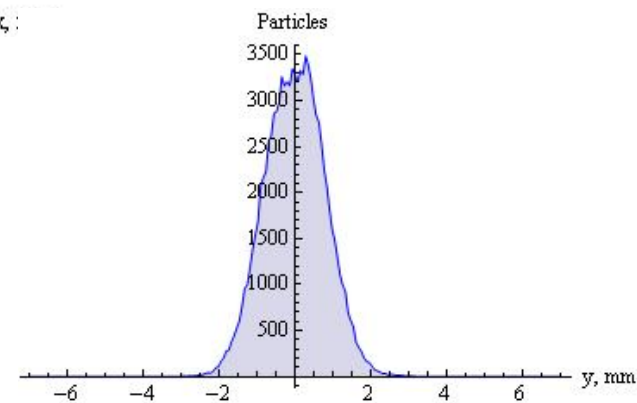
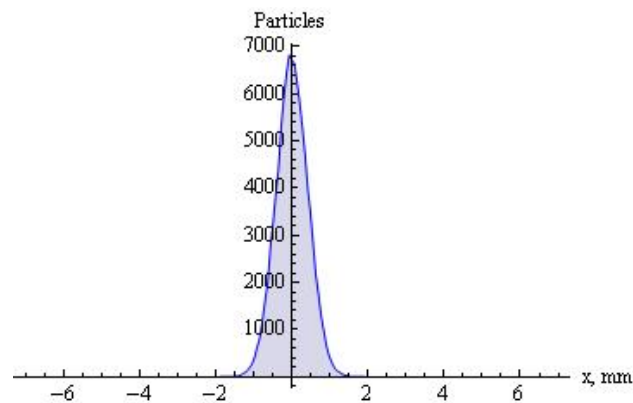


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Simulation results
electrons spatial distribution
on the screen monitor $\varphi=0$



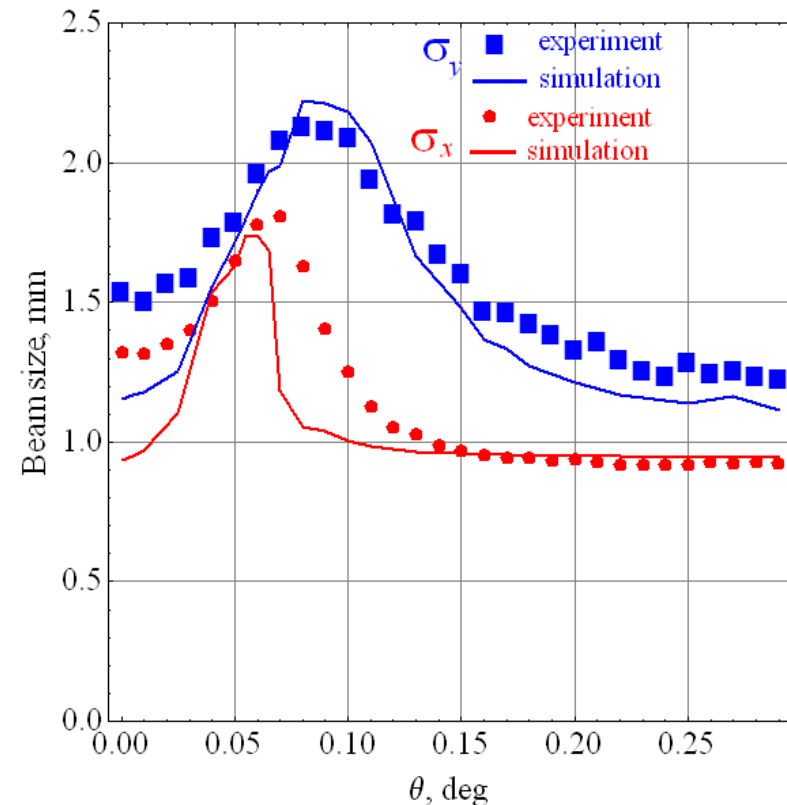
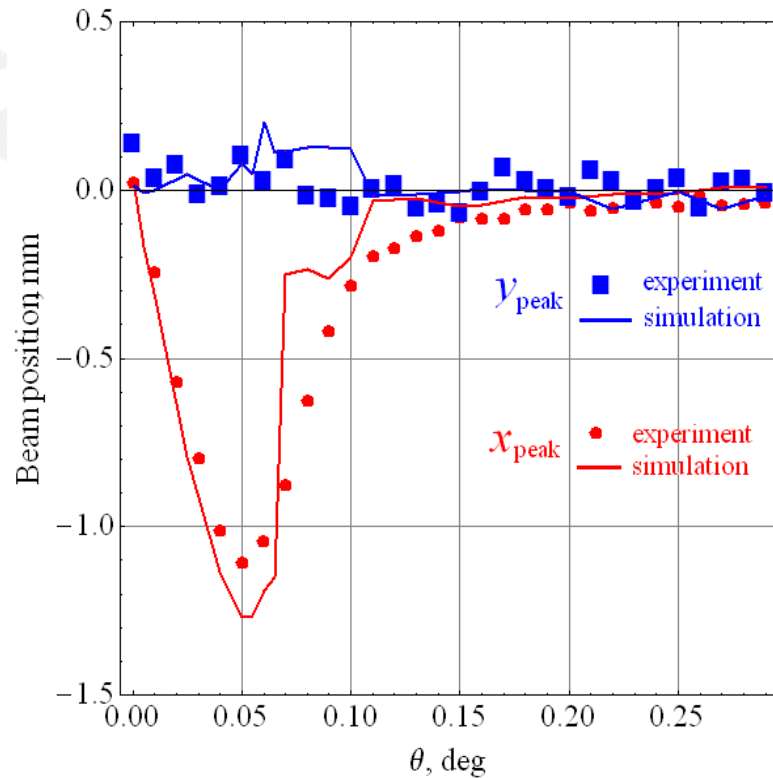
$\theta = \{0.0, 0.005, 0.01, 0.025, 0.04, 0.05, 0.055, 0.06, 0.065, 0.07, 0.08, 0.09, 0.1, 0.11, 0.13, 0.15, 0.16, 0.17, 0.18, 0.2, 0.22, 0.25, 0.27, 0.29\};$



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Simulation results

beam position and beam size



$$\sigma = \sqrt{\sigma_{\text{simulation}}^2 + \sigma_{ms}^2} \quad \theta_{ms} = \mathbf{0.4 \text{ mrad}}$$

Future plans for SAGA LS – TPU collaboration

- ❑ Scattering at planar channeling condition (silicon crystal, $L=20$ micrometers, electron energy 255 MeV) – the experiment has been recently performed, data processing and computer simulation are in progress
- ❑ Scattering in a thin silicon crystal ($L=1$ micrometer, electron energy 255 MeV)
- ❑ Scattering in a diamond crystal ($L=50$ micrometers, electron energy 255 MeV)
- ❑ Further studies of PXR, PXRC, DCR
- ❑ Further development of theory and simulation methods

Conclusions

- ❑ The first experiments on 255 MeV electrons channeling and scattering in thin aligned Si crystal were performed at SAGA-LS injector Linac
- ❑ The simulation of trajectories at the $\langle 100 \rangle$ axial channeling in Si, angular and spatial distributions of electrons on the screen monitor have been performed taking into account initial spatial and angular beam divergence of the electron beam
- ❑ Comparison of the experimental and theoretical results shows a quite good agreement
- ❑ Both experimental data and simulations show the brilliant effect of so-called «doughnut scattering»
- ❑ Application of electrons «doughnut scattering»: possibility to use for the beam diagnostics

Details of experiment and simulations:

O. V. Bogdanov, Yu. L. Pivovarov, Y. Takabayashi, T.A. Tukhfatullin
Journal of Physics: Conf. Ser. 357 (2012) 012030.

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Thank you for attention

(220) PLANAR CHANNELING

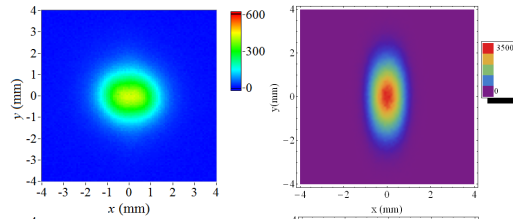
Beam profile

experiment

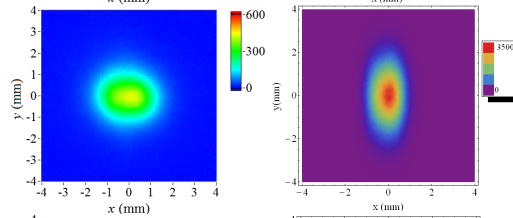
simulation

(θ, φ)

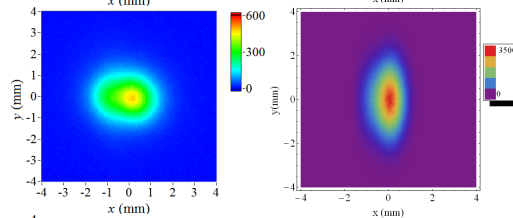
$(0.00^\circ, 1^\circ)$



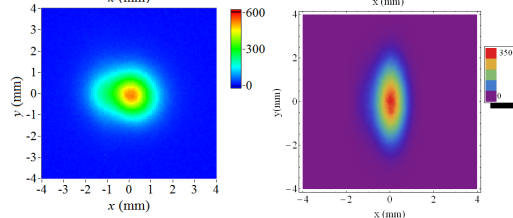
$(0.01^\circ, 1^\circ)$



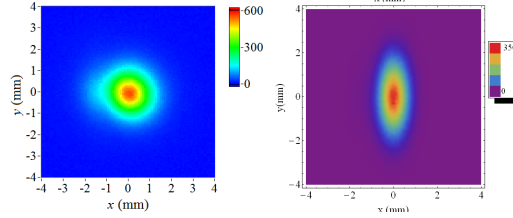
$(0.02^\circ, 1^\circ)$



$(0.03^\circ, 1^\circ)$



$(0.04^\circ, 1^\circ)$



Beam position and size vs incident angle

Critical channeling angle 0.023°

initial vertical beam size - $\sigma_x=0.2$ mm, horizontal beam size - $\sigma_y=0.9$ mm

horizontal angular beam divergence - 0.2 mrad

vertical angular beam divergence - 0.3 mrad

